

FQB8N90C

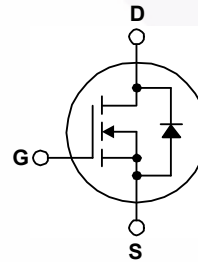
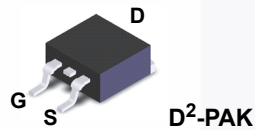
N-Channel QFET® MOSFET 900 V, 6.3 A, 1.9 Ω

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies.

Features

- 6.3 A, 900 V, $R_{DS(on)} = 1.9 \Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$
- Low Gate Charge (Typ. 35 nC)
- Low C_{rss} (Typ. 12 pF)
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQB8N90CTM	Unit
V_{DSS}	Drain-Source Voltage	900	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	6.3	A
		3.8	A
I_{DM}	Drain Current - Pulsed (Note 1)	25	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	850	mJ
I_{AR}	Avalanche Current (Note 1)	6.3	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	17.1	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate Above 25°C	171	W
		1.37	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQB8N90CTM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.73	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB8N90CTM	FQB8N90C	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	900	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.95	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 900\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 720\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3.15\text{ A}$	--	1.6	1.9	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 3.15\text{ A}$	--	5.5	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1600	2080	pF
C_{oss}	Output Capacitance		--	130	170	pF
C_{rss}	Reverse Transfer Capacitance		--	12	15	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 450\text{ V}, I_D = 8\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 25\ \Omega$	--	40	90	ns	
t_r	Turn-On Rise Time		--	110	230	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4)	--	70	150	ns
t_f	Turn-Off Fall Time		(Note 4)	--	70	150	ns
Q_g	Total Gate Charge	$V_{DS} = 720\text{ V}, I_D = 8\text{ A},$ $V_{GS} = 10\text{ V}$	--	35	45	nC	
Q_{gs}	Gate-Source Charge		(Note 4)	--	10	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	14	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	6.3	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	25	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 6.3\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 8\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	530	--	ns
Q_{rr}	Reverse Recovery Charge		--	5.8	--	μC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. $L = 40\text{ mH}, I_{AS} = 6.3\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 8\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Characteristics

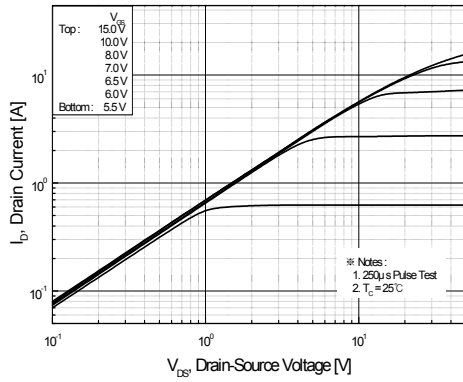


Figure 1. On-Region Characteristics

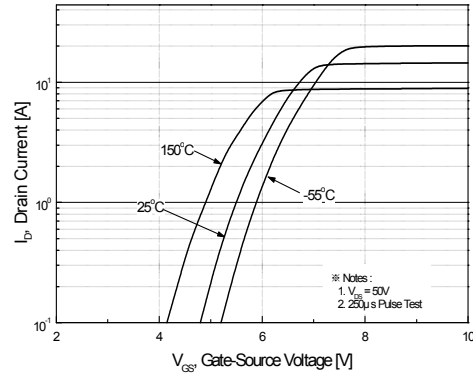


Figure 2. Transfer Characteristics

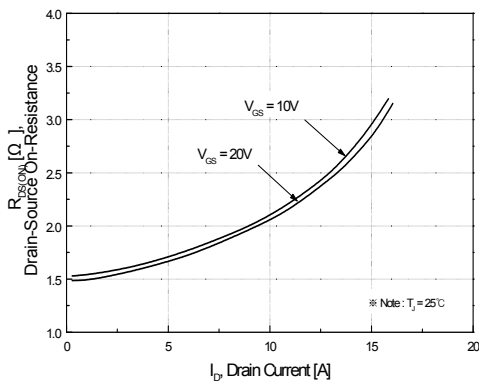


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

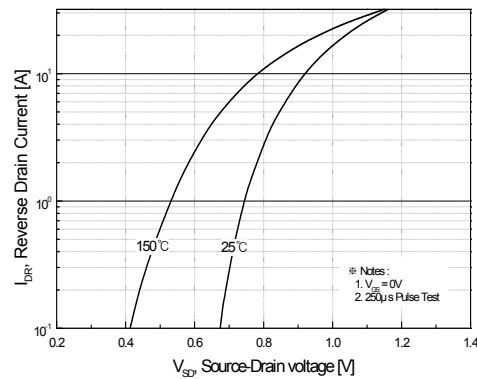


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

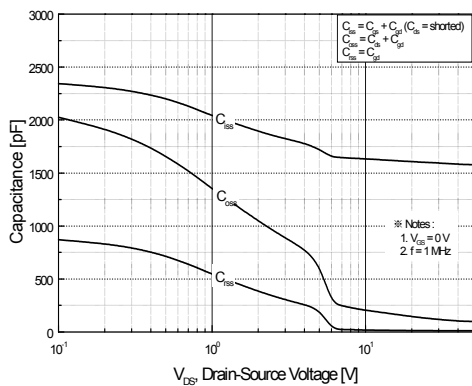


Figure 5. Capacitance Characteristics

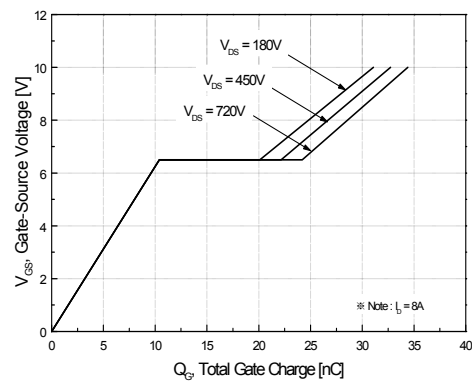


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

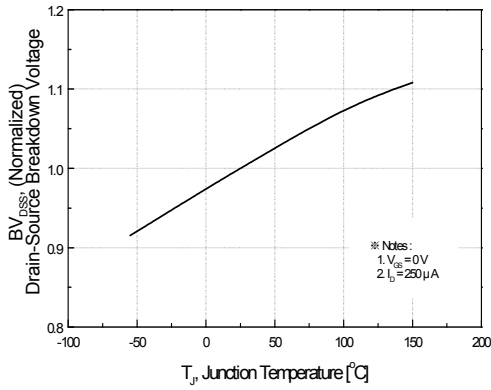


Figure 7. Breakdown Voltage Variation vs Temperature

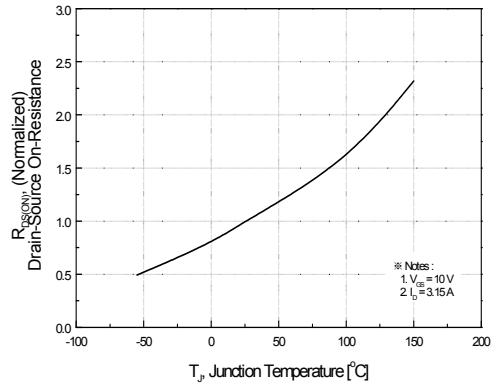


Figure 8. On-Resistance Variation vs Temperature

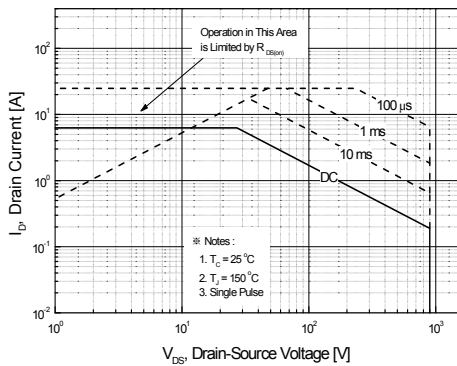


Figure 9. Maximum Safe Operating Area

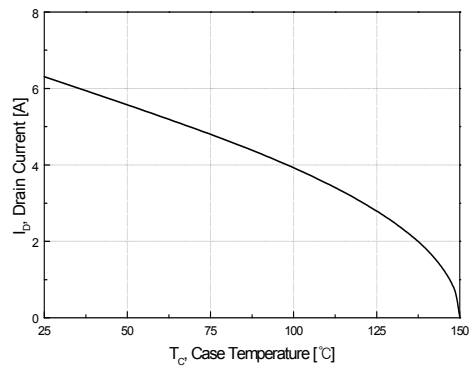


Figure 10. Maximum Drain Current vs Case Temperature

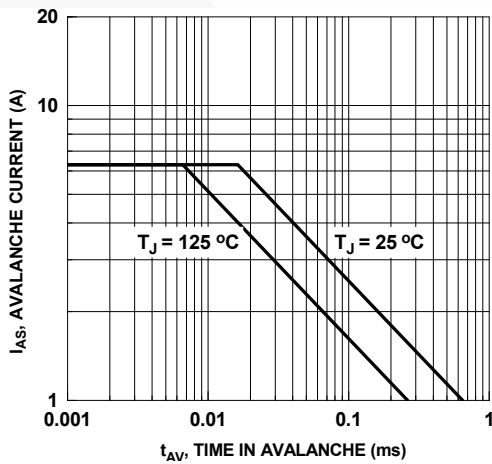


Figure 11. Unclamped Inductive Switching Capability

Typical Characteristics (Continued)

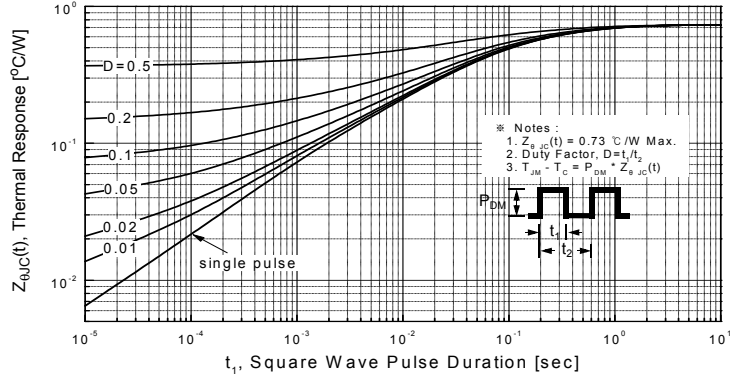


Figure 12. Transient Thermal Response Curve



Figure 13. Gate Charge Test Circuit & Waveform



Figure 14. Resistive Switching Test Circuit & Waveforms



Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



Figure 17. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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